PDTC114E series

NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

Rev. 12 — 21 December 2011

Product data sheet

1. Product profile

1.1 General description

NPN Resistor-Equipped Transistor (RET) family in small Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package	_			Package	
	NXP	JEITA	JEDEC	complement	configuration	
PDTC114EE	SOT416	SC-75	'-	PDTA114EE	ultra small	
PDTC114EM	SOT883	SC-101	-	PDTA114EM	leadless ultra small	
PDTC114ET	SOT23	-	TO-236AB	PDTA114ET	small	
PDTC114EU	SOT323	SC-70	-	PDTA114EU	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital application in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		7	10	13	$k\Omega$
R2/R1	bias resistor ratio		0.8	1.0	1.2	



2. Pinning information

Table 3. Pinning

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
SOT23; S	SOT323; SOT416		
1	input (base)		
2	GND (emitter)	[3]	R1 3
3	output (collector)	1 2 006aaa144	1 R2 R2 sym007
SOT883			
1	input (base)		
2	GND (emitter)	1 3	3
3	output (collector)	2 Transparent top view	1 R1 R2 sym007

3. Ordering information

Table 4. Ordering information

Type number	Package						
	Name	Description	Version				
PDTC114EE	SC-75	plastic surface-mounted package; 3 leads	SOT416				
PDTC114EM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883				
PDTC114ET	-	plastic surface-mounted package; 3 leads	SOT23				
PDTC114EU	SC-70	plastic surface-mounted package; 3 leads	SOT323				

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PDTC114EE	09
PDTC114EM	DS
PDTC114ET	*16
PDTC114EU	*09

^{[1] * =} placeholder for manufacturing site code.

5. Limiting values

Table 6. Limiting values

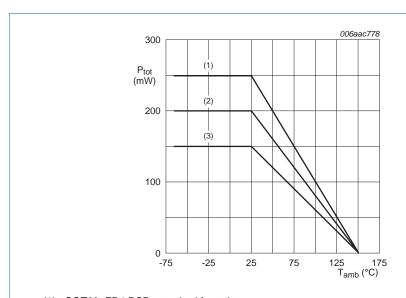
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	ı	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	-	10	V
VI	input voltage					
	positive		_	•	+40	V
	negative		-	-	-10	V
Io	output current		_	•	100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	_	•	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C				
	PDTC114EE (SOT416)		[1][2]	•	150	mW
	PDTC114EM (SOT883)		[2][3]	-	250	mW
	PDTC114ET (SOT23)		<u>[1]</u> -	-	250	mW
	PDTC114EU (SOT323)		[1] -	-	200	mW
Tj	junction temperature		-	-	150	°C
T _{amb}	ambient temperature		-	-65	+150	°C
T _{stg}	storage temperature		-	-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

^[3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



- (1) SOT23; FR4 PCB, standard footprint SOT883; FR4 PCB with 70 μm copper strip line, standard footprint
- (2) SOT323; FR4 PCB, standard footprint
- (3) SOT416; FR4 PCB, standard footprint

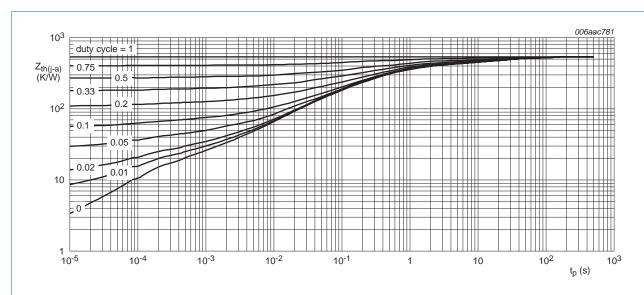
Fig 1. Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

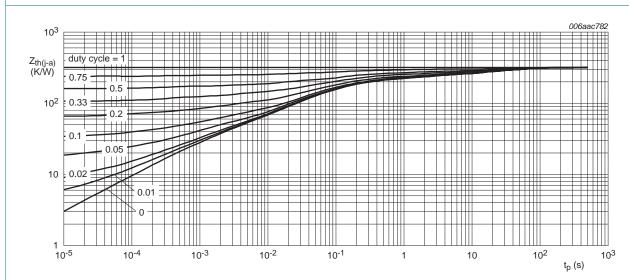
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PDTC114EE (SOT416)		[1][2]	-	830	K/W
	PDTC114EM (SOT883)		[2][3]	-	500	K/W
	PDTC114ET (SOT23)		<u>[1]</u> -	-	500	K/W
	PDTC114EU (SOT323)		<u>[1]</u> _	-	625	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC114EE (SOT416); typical values



FR4 PCB, 70 µm copper strip line

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC114EM (SOT883); typical values

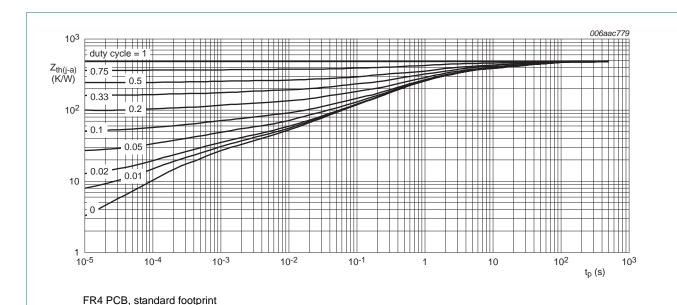


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC114ET (SOT23); typical values

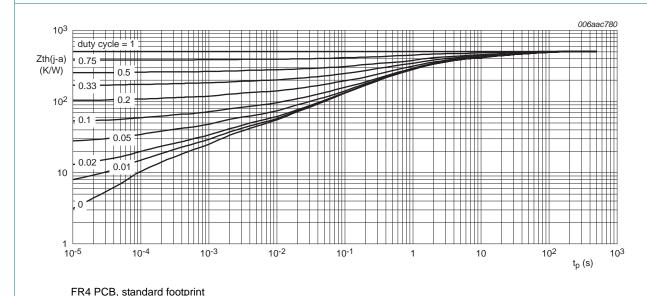


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC114EU (SOT323); typical values

NPN resistor-equipped transistors; R1 = 10 kΩ, R2 = 10 kΩ

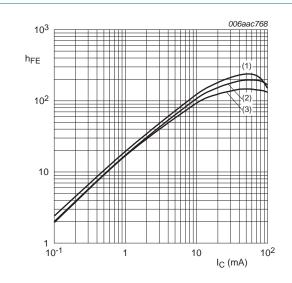
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

amb — 20	O unicos outerwise sp	comea.					
Symbol	Parameter	Conditions	N	lin	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-		-	100	nA
OLO TIME	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-		-	1	μΑ
	cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-		-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$	-		-	400	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	3	0	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-		-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-		1.1	0.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 10 \text{ mA}$	2	.5	1.8	-	V
R1	bias resistor 1 (input)		7		10	13	kΩ
R2/R1	bias resistor ratio		0	.8	1.0	1.2	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-		-	2.5	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA;}$ f = 100 MHz	[1] -		230	-	MHz

^[1] Characteristics of built-in transistor.



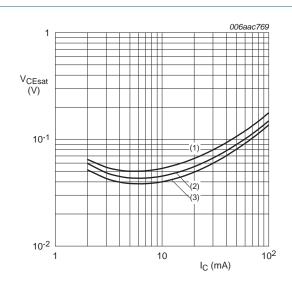
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 6. DC current gain as a function of collector current; typical values



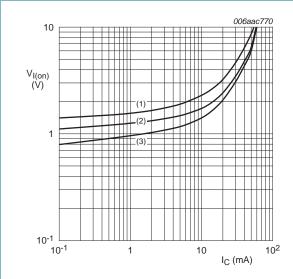
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values

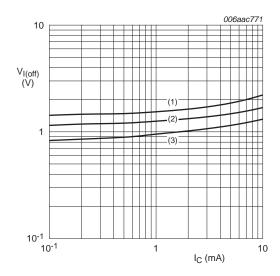


$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

Fig 8. On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 9. Off-state input voltage as a function of collector current; typical values

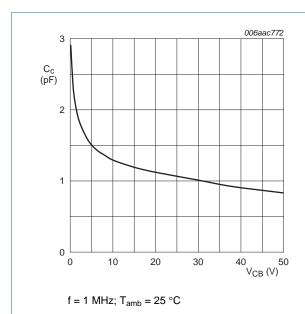


Fig 10. Collector capacitance as a function of collector-base voltage; typical values

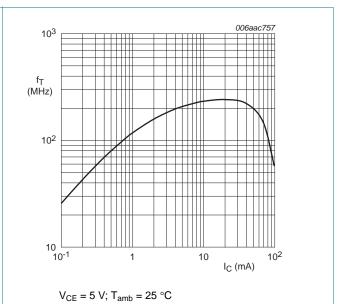


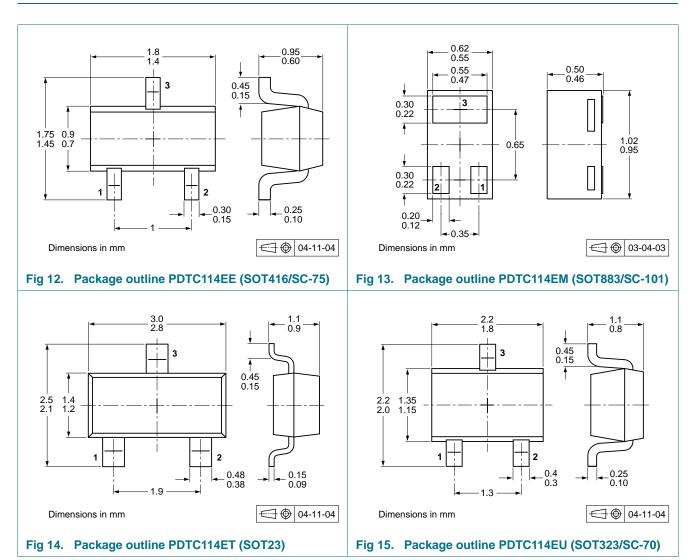
Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

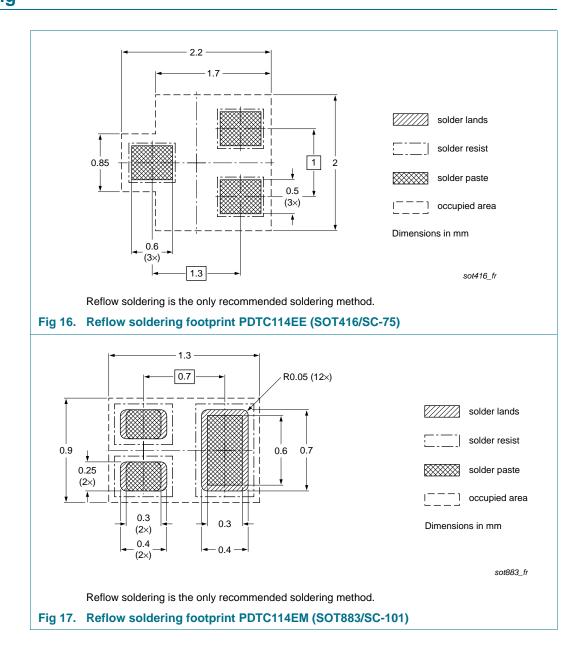
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

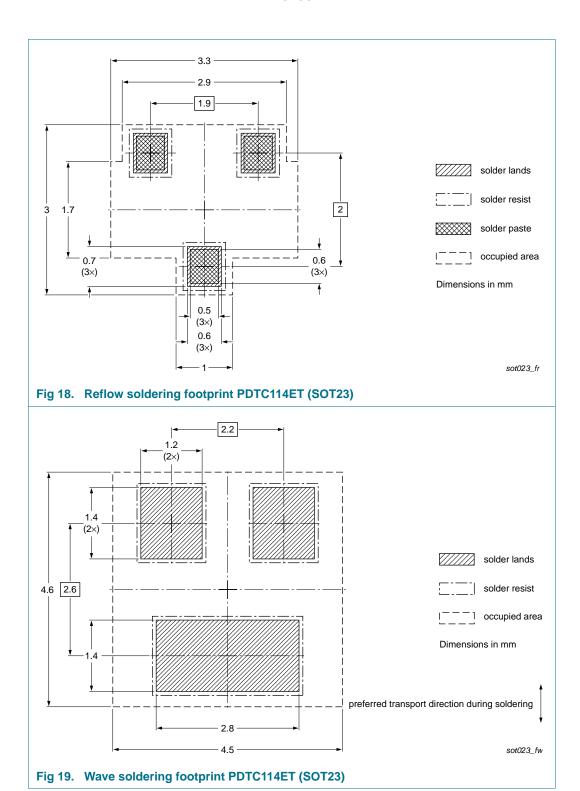
Type number	Package	Description	Packing	Packing quantity		
			3000	10000		
PDTC114EE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-135		
PDTC114EM	SOT883	2 mm pitch, 8 mm tape and reel	-	-315		
PDTC114ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235		
PDTC114EU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135		

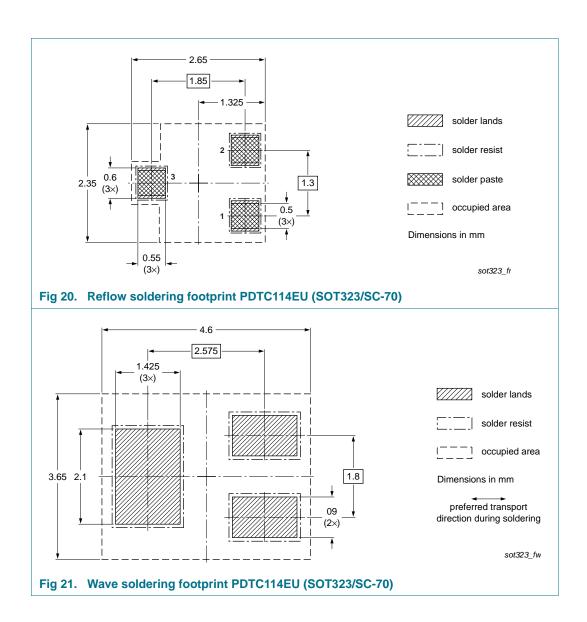
^[1] For further information and the availability of packing methods, see $\underline{\text{Section 14}}$.

PDTC114E_SER

11. Soldering







NPN resistor-equipped transistors; R1 = 10 kΩ, R2 = 10 kΩ

12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTC114E_SER v.12	20111221	Product data sheet	-	PDTC114E_SER v.11
Modifications:	• Figure 3 and	d <u>5</u> : corrected		
PDTC114E_SER v.11	20111121	Product data sheet	-	PDTC114E_SERIES v.10
PDTC114E_SERIES v.10	20040805	Product specification	-	PDTC114E_SERIES v.9
PDTC114E_SERIES v.9	20030410	Product specification	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PDTC114E_SER

PDTC114E series

NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

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PDTC114E series

NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

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